

PREFACE

This volume contains the peer reviewed digests from the 7th European Conference on Silicon Carbide and Related Materials (ECSCRM 2008). The conference was held on September 7-11 in Barcelona, Spain following the successful preceding meetings held at Crete, Montpellier, Kloster Banz, Linköping, Bologna and Newcastle. ECSCRM provides a bi-annual academia/industry forum for technical discussion in the area of Silicon Carbide and related materials, as a substrate for wide-band gap electronics. Over the years, this conference has matured and is presently regarded as the leading European conference in the field. Furthermore, the ECSCRM conference is *de facto* international.

The total number of submitted abstracts was 292. The truly global nature of ECSCRM is reflected by the fact that contributions originated from a total of 27 countries: 51% from Europe, 22% from Japan, 15% from the USA and 7% from the rest of the world. This year, the conference attracted a higher degree of participation from several countries such as Poland, India and China. The program committee selected 43 papers for oral presentation, 13 of which were invited. Three “best student paper” accolades were presented, awarded by Acreo/MANSiC.

This volume has been arranged into seven chapters. The topics covered include SiC and related materials bulk and epi growth, characterization of SiC and related materials technology, devices and applications. Novel subject areas that displayed a strong increase of contributions include cutting-edge SiC nanostructures and graphene. From the scientific point of view, we have seen that bipolar degradation can be significantly reduced by appropriate material preparation. Cubic Silicon Carbide is once again attracting attention from both researchers and industry. It has also been shown that the reliability of MOS structures on SiC is improving. Moreover, we have seen a step-change increase in the application of SiC technologies within renewable energy systems and space domains. Undoubtedly, a close examination of this volume will empower the reader with a clear state-of-the-art overview of the field.

The success of this conference is due to the dedication of many people, in particular the members of the Steering, Program and Organizing Committees. I would also like to thank our Sponsors, the session chairpersons and the paper reviewers. I am grateful to each of the CNM people for their dedication and professionalism in delivering a demanding schedule of work. Mihaela Alexandru, Viorel Banu, Maxime Berthou, Lourdes Carreras, Aurore Constant, Teresa González., Iñigo Martín, Annabel Muñoz, David Sánchez, and Monica Sarrión, thank you!

The next conference of this series travels north. ECSCRM 2010 will take place in Oslo, Norway, chaired by Prof. Bengt Svensson. I would like to take this opportunity to wish the organizers of the next conference much success.

Barcelona, September, 2008

Philippe Godignon